Masao Sakuraba

List of Publications by Year
in descending order

141 papers	1,111 citations	471061 17 h-index	552369 26 g-index
141 all docs	141 docs citations	141 times ranked	478 citing authors

#	Article	IF	Citations
1	Atomically Controlled Processing for Group IV Semiconductors by Chemical Vapor Deposition. Japanese Journal of Applied Physics, 2006, 45, 6767-6785.	0.8	84
2	Silicon atomic layer growth controlled by flash heating in chemical vapor deposition using SiH4gas. Applied Physics Letters, 1993, 62, 2353-2355.	1.5	45
3	Stability of the dimer structure formed on Si(100) by ultraclean lowâ€pressure chemicalâ€vapor deposition. Journal of Applied Physics, 1994, 75, 3701-3703.	1.1	40
4	Atomically controlled processing for group IV semiconductors. Surface and Interface Analysis, 2002, 34, 423-431.	0.8	40
5	Atomicâ€Order Thermal Nitridation of Silicon at Low Temperatures. Journal of the Electrochemical Society, 1998, 145, 4252-4256.	1.3	35
6	Separation between Surface Adsorption and Reaction of NH3on Si(100) by Flash Heating. Japanese Journal of Applied Physics, 1999, 38, 515-517.	0.8	26
7	Atomic layer epitaxy of germanium on silicon using flash heating chemical vapor deposition. Journal of Crystal Growth, 1991, 115, 79-82.	0.7	25
8	Atomic-layer adsorption of P on Si(100) and Ge(100) by PH3 using an ultraclean low-pressure chemical vapor deposition. Applied Surface Science, 2000, 162-163, 390-394.	3.1	25
9	Thermal nitridation of ultrathin SiO2 on Si by NH3. Surface and Interface Analysis, 2002, 34, 456-459.	0.8	25
10	Effects of interfacial chemical states on the performance of perovskite solar cells. Journal of Materials Chemistry A, 2016, 4, 4392-4397.	5.2	25
11	Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH4 and SiH4 gases. Applied Surface Science, 1994, 82-83, 354-358.	3.1	24
12	Doping and electrical characteristics of in-situ heavily B-doped Si1â^'xâ^'yGexCy films epitaxially grown using ultraclean LPCVD. Thin Solid Films, 2000, 380, 57-60.	0.8	23
13	Low-temperature reaction of CH4 on Si(100). Journal of Crystal Growth, 1998, 188, 131-136.	0.7	21
14	Atomic-layer doping in Si by alternately supplied NH3 and SiH4. Applied Physics Letters, 2003, 82, 3472-3474.	1.5	21
15	Initial growth characteristics of germanium on silicon in LPCVD using germane gas. Journal of Crystal Growth, 1997, 174, 686-690.	0.7	19
16	Surface reaction of CH3SiH3 on Ge(100) and Si(100). Applied Surface Science, 2000, 162-163, 156-160.	3.1	19
17	Epitaxial growth of Si 1â^'xâ^'y Ge x C y film on Si(100) in a SiH 4 -GeH 4 -CH 3 SiH 3 reaction. Thin Solid Films, 2000, 369, 167-170.	0.8	18
18	Atomic-layer doping in Si by alternately supplied PH3 and SiH4. Thin Solid Films, 2000, 380, 134-136.	0.8	18

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19	Formation of heavily P-doped Si epitaxial film on Si(100) by multiple atomic-layer doping technique. Applied Surface Science, 2004, 224, 202-205.	3.1	18
20	Improvement in negative differential conductance characteristics of hole resonant-tunneling diodes with high Ge fraction Si/strained Si1â^'Ge /Si(1 0 0) heterostructure. Solid-State Electronics, 2009, 53, 912-915.	0.8	17
21	Atomic-Layer Surface Reaction ofSiH4on Ge(100). Japanese Journal of Applied Physics, 1997, 36, 4042-4045.	0.8	16
22	Amphiphobic Septa Enhance the Mechanical Stability of Free-Standing Bilayer Lipid Membranes. Langmuir, 2018, 34, 5615-5622.	1.6	16
23	Doping and electrical characteristics of in situ heavily B-doped Si1â^'xGex films epitaxially grown using ultraclean LPCVD. Thin Solid Films, 1999, 343-344, 541-544.	0.8	15
24	Observation of sharp current peaks in resonant tunneling diode with strained Si0.6Ge0.4/Si(100) grown by low-temperature low-pressure CVD. Journal of Crystal Growth, 2000, 209, 315-320.	0.7	15
25	Atomically Controlled Technology for Future Si-Based Devices. Solid State Phenomena, 2004, 95-96, 607-616.	0.3	15
26	Si self-diffusivity using isotopically pure 30Si epitaxial layers. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2004, 114-115, 330-333.	1.7	15
27	Segregation and diffusion of phosphorus from doped Si1â^'xGex films into silicon. Journal of Applied Physics, 1999, 86, 5480-5483.	1.1	14
28	Very low-temperature epitaxial growth of silicon and germanium using plasma-assisted CVD. Thin Solid Films, 2008, 517, 10-13.	0.8	14
29	Structure and optical properties of Si and SiGe layers grown on SiO2 by chemical vapor deposition. Thin Solid Films, 2015, 579, 131-135.	0.8	14
30	Contact resistivity between tungsten and impurity (P and B)-doped Si1â^'â^'Ge C epitaxial layer. Applied Surface Science, 2003, 212-213, 679-683.	3.1	13
31	Thermal effect on strain relaxation in Ge films epitaxially grown on Si(100) using ECR plasma CVD. Thin Solid Films, 2006, 508, 143-146.	0.8	13
32	Strain relaxation by stripe patterning in Si/Si1â^'xGex/Si(100) heterostructures. Thin Solid Films, 2006, 508, 239-242.	0.8	13
33	Fabrication of 0.12 Î¼m pMOSFETs on high Ge fraction Si/Si1â^'xGex/Si(1 0 0) heterostructure with ultrashallow source/drain formed using B-doped SiGe CVD. Applied Surface Science, 2004, 224, 254-259.	3.1	11
34	Hole tunnelling properties in resonant tunnelling diodes with Si/strained Si0.8Ge0.2 heterostructures grown on Si(1â€‰0â€‰0) by low-temperature ultraclean LPCVD. Semiconductor Science and Technology, 2007, 22, S38-S41.	1.0	11
35	Heavy B atomic-layer doping characteristics in Si epitaxial growth on B adsorbed Si(1 0 0) by ultraclean low-pressure CVD system. Solid-State Electronics, 2009, 53, 877-879.	0.8	11
36	Fabrication of high-Ge-fraction strained Si1â^'Ge /Si hole resonant tunneling diode using low-temperature Si2H6 reaction for nanometer-order ultrathin Si barriers. Solid-State Electronics, 2011, 60, 112-115.	0.8	11

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37	Segregation and diffusion of impurities from doped Si 1â^'x Ge x films into silicon. Thin Solid Films, 2000, 369, 222-225.	0.8	10
38	Ar plasma irradiation effects in atomically controlled Si epitaxial growth. Applied Surface Science, 2004, 224, 210-214.	3.1	10
39	Atomically controlled Ge epitaxial growth on Si(100) in Ar-plasma-enhanced GeH4 reaction. Materials Science in Semiconductor Processing, 2005, 8, 69-72.	1.9	10
40	Heavy atomic-layer doping of B in low-temperature Si epitaxial growth on Si(100) by ultraclean low-pressure chemical vapor deposition. Applied Surface Science, 2008, 254, 6086-6089.	3.1	10
41	Phosphorus Doping in Si1-x-yGexCyEpitaxial Growth by Low-Pressure Chemical Vapor Deposition Using a SiH4â€“GeH4â€“CH3SiH3â€“PH3â€“H2Gas System. Japanese Journal of Applied Physics, 2001, 40, 2697-2700.	0.8	9
42	Atomic-order thermal nitridation of Si(100) and subsequent growth of Si. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2001, 19, 1907-1911.	0.9	9
43	Relationship between impurity (B or P) and carrier concentration in SiGe(C) epitaxial film produced by thermal treatment. Applied Surface Science, 2004, 224, 77-81.	3.1	8
44	Epitaxial growth of P atomic layer doped Si film by alternate surface reactions of PH3and Si2H6on strained Si1â^'xGex/Si(1â€‰0â€‰0) in ultraclean low-pressure CVD. Semiconductor Science and Technology, 2007, 22, S118-S122.	1.0	8
45	Heavy carbon atomic-layer doping at Si1â^'Ge /Si heterointerface. Thin Solid Films, 2010, 518, S222-S225.	0.8	8
46	Super self-aligned technology of ultra-shallow junction in MOSFETs using selective Si1â^'xGex CVD. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2002, 89, 120-124.	1.7	7
47	Epitaxial growth of N delta doped Si films on Si(1 0 0) by alternately supplied NH3 and SiH4. Applied Surface Science, 2004, 224, 197-201.	3.1	7
48	Carbon effect on strain compensation in Si1â^'xâ^'yGexCy films epitaxially grown on Si(100). Thin Solid Films, 2006, 508, 140-142.	0.8	7
49	Photo detection characteristics of Si/Si1â^'xGex/Si p-i-n diodes integrated with optical waveguides. Thin Solid Films, 2006, 508, 399-401.	0.8	7
50	High Ge fraction intrinsic SiGe-heterochannel MOSFETs with embedded SiGe source/drain electrode formed by in-situ doped selective CVD epitaxial growth. Thin Solid Films, 2008, 517, 346-349.	0.8	7
51	Impact of Si cap layer growth on surface segregation of P incorporated by atomic layer doping. Thin Solid Films, 2010, 518, S231-S233.	0.8	7
52	Epitaxial growth of Si1â^'xGex alloys and Ge on Si(100) by electron-cyclotron-resonance Ar plasma chemical vapor deposition without substrate heating. Thin Solid Films, 2014, 557, 31-35.	0.8	7
53	Atomic Layer-by-Layer Epitaxy of Silicon and Germanium Using Flash Heating in CVD. European Physical Journal Special Topics, 1995, 05, C5-1101-C5-1108.	0.2	6
54	Si atomic layer-by-layer epitaxial growth process using alternate exposure of Si(1 0 0) to SiH4 and to Ar plasma. Applied Surface Science, 2003, 212-213, 197-200.	3.1	6

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55	Sidewall protection by nitrogen and oxygen in poly-Si1â^'xGex anisotropic etching using Cl2/N2/O2 plasma. Materials Science in Semiconductor Processing, 2005, 8, 239-243.	1.9	6
56	Integration of Si pâ€“iâ€“n diodes for light emitter and detector with optical waveguides. Materials Science in Semiconductor Processing, 2005, 8, 435-438.	1.9	6
57	Impact of Ge fraction modulation upon electrical characteristics of hole resonant tunneling diodes with Si/Strained Si1â^'Ge /Si(100) heterostructure. Thin Solid Films, 2008, 517, 110-112.	0.8	6
58	Atomically Controlled Plasma Processing for Group IV Quantum Heterostructure Formation. Key Engineering Materials, 2011, 470, 98-103.	0.4	6
59	Carrier properties of B atomic-layer-doped Si films grown by ECR Ar plasma-enhanced CVD without substrate heating. Science and Technology of Advanced Materials, 2017, 18, 294-306.	2.8	6
60	Drain leakage current and instability of drain current in Si/Si 1â^'x Ge x MOSFETs. Thin Solid Films, 2000, 369, 379-382.	0.8	5
61	Electrical properties of N atomic layer doped Si epitaxial films grown by ultraclean low-pressure chemical vapor deposition. Materials Science in Semiconductor Processing, 2005, 8, 121-124.	1.9	5
62	Epitaxial growth of highly strained Si on relaxed Ge/Si(1â€‰0â€‰0) using ECR plasma CVD without substrate heating. Semiconductor Science and Technology, 2007, 22, S42-S45.	1.0	5
63	Fabrication of Hole Resonant Tunneling Diodes with Nanometer Order Heterostructures of Si/Strained Si_{1-x}Ge_x Epitaxially Grown on Si(100). ECS Transactions, 2007, 11, 131-139.	0.3	5
64	Surface Reaction in Thin Film Formation of Si1-xGex Alloys on Si(100) by Electron-Cyclotron-Resonance Ar Plasma Chemical Vapor Deposition without Substrate Heating. ECS Transactions, 2014, 64, 99-105.	0.3	5
65	Si epitaxial growth on SiH3CH3 reacted Ge(1 0 0) and intermixing between Si and Ge during heat treatment. Applied Surface Science, 2003, 212-213, 193-196.	3.1	4
66	W delta doping in Si(1 0 0) using ultraclean low-pressure CVD. Applied Surface Science, 2003, 212-213, 684-688.	3.1	4
67	Proposal of a multi-layer channel MOSFET: the application of selective etching for Si/SiGe stacked layers. Applied Surface Science, 2004, 224, 270-273.	3.1	4
68	Characterization of hot-carrier degraded SiGe/Si-hetero-PMOSFETs. Thin Solid Films, 2006, 508, 326-328.	0.8	4
69	Effect of grain boundary on electrical characteristics in B- and P-doped polycrystalline Si1â^'xâ^'yGexCy film deposited by ultraclean LPCVD. Thin Solid Films, 2006, 508, 36-39.	0.8	4
70	Carbon doping effect on strain relaxation during Si1â^'xâ^'yGexCy epitaxial growth on Si(1â€‰0â€‰0) at 500 Â°C. Semiconductor Science and Technology, 2007, 22, S5-S8.	1.0	4
71	Strain control and electrical properties of stripe-patterned Si/Si1â^'xGex/Si(1â€‰0â€‰0) heterostructures. Semiconductor Science and Technology, 2007, 22, S33-S37.	1.0	4
72	Electrical characteristics of hole resonant tunneling diodes with high Ge fraction (x>0.4) Si/strained Si1â^'xGex/Si(100) heterostructure. Applied Surface Science, 2008, 254, 6265-6267.	3.1	4

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73	Local strain in Si/Si0.6Ge0.4/Si(100) heterostructures by stripe-shape patterning. Thin Solid Films, 2008, 517, 300-302.	0.8	4
74	Si epitaxial growth on self-limitedly B adsorbed Si1â˜'Ge (100) by ultraclean low-pressure CVD system. Thin Solid Films, 2008, 517, 229-231.	0.8	4
75	Heavy atomic-layer doping of nitrogen in Si1â˜'Ge film epitaxially grown on Si(100) by ultraclean low-pressure CVD. Thin Solid Films, 2010, 518, S62-S64.	0.8	4
76	Heavy B atomic-layer doping in Si epitaxial growth on Si(100) using electron-cyclotron-resonance plasma CVD. Thin Solid Films, 2010, 518, S140-S142.	0.8	4
77	Epitaxial growth of B-doped Si on Si(100) by electron-cyclotron-resonance Ar plasma chemical vapor deposition in a SiH4â€“B2H6â€“H2 gas mixture without substrate heating. Thin Solid Films, 2014, 557, 10-13.	0.8	4
78	Electronic properties of Si/Si-Ge Alloy/Si(100) heterostructures formed by ECR Ar plasma CVD without substrate heating. Materials Science in Semiconductor Processing, 2017, 70, 55-62.	1.9	4
79	An Izhikevich Model Neuron MOS Circuit for Low Voltage Operation. Lecture Notes in Computer Science, 2019, , 718-723.	1.0	4
80	Layer-by-layer growth of silicon nitride films by NH₃ and SiH₄. European Physical Journal Special Topics, 1999, 09, Pr8-333-Pr8-340.	0.2	4
81	Effect of Si/Si 1- y C y /Si Barriers on the Characteristics of Si 1- x Ge x /Si Resonant Tunneling Structures. Chinese Physics Letters, 2000, 17, 844-846.	1.3	3
82	Work function of impurity-doped polycrystalline Si1â˜'â˜'Ge C film deposited by ultraclean low-pressure CVD. Applied Surface Science, 2003, 212-213, 209-212.	3.1	3
83	Atomically Controlled Impurity Doping in Si-Based CVD Epitaxial Growth. Materials Research Society Symposia Proceedings, 2004, 809, B10.1.1.	0.1	3
84	Effect of carbon on the thermal stability of a Si atomic layer on Ge(1 0 0). Applied Surface Science, 2004, 224, 206-209.	3.1	3
85	Behavior of N atoms in atomic-order nitrided Si0.5Ge0.5(100). Applied Surface Science, 2008, 254, 6021-6024.	3.1	3
86	Atomically Controlled Processing in Silicon-Based CVD Epitaxial Growth. Journal of Nanoscience and Nanotechnology, 2011, 11, 8348-8353.	0.9	3
87	Epitaxial Growth of Heavily B-Doped Si and Ge Films on Si(100) by Low-Energy ECR Ar Plasma CVD without Substrate Heating. ECS Transactions, 2013, 58, 223-228.	0.3	3
88	Izhikevich neuron circuit using stochastic logic. Electronics Letters, 2014, 50, 1795-1797.	0.5	3
89	Electrical properties of W delta doped Si epitaxial films grown on Si(100) by ultraclean low-pressure chemical vapor deposition. Materials Science in Semiconductor Processing, 2005, 8, 125-129.	1.9	2
90	Si epitaxial growth on atomic-order nitrided Si(1 0 0) using electron cyclotron resonance plasma. Materials Science in Semiconductor Processing, 2005, 8, 65-68.	1.9	2

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91	A Study on B Atomic Layer Formation for B-Doped Si1-xGex(100) Epitaxial Growth Using Ultraclean LPCVD System. ECS Transactions, 2006, 3, 861-866.	0.3	2
92	Hot Carrier Degradation of SiGe/Si Heterointerface and Experimental Estimation of Density of Locally Generated Heterointerface Traps. Japanese Journal of Applied Physics, 2007, 46, 5015.	0.8	2
93	Self-limited growth of Si on B atomic-layer formed Ge(100) by ultraclean low-pressure CVD system. Applied Surface Science, 2008, 254, 6090-6093.	3.1	2
94	Structural change of atomic-order nitride formed on Si1â^'Ge (100) and Ge(100) by heat treatment. Thin Solid Films, 2008, 517, 219-221.	0.8	2
95	Electrical characteristics of thermal CVD B-doped Si films on highly strained Si epitaxially grown on Ge(100) by plasma CVD without substrate heating. Thin Solid Films, 2010, 518, S57-S61.	0.8	2
96	Room-Temperature Resonant Tunneling Diode with High-Ge-Fraction Strained Si1-xGex and Nanometer-Order Ultrathin Si. ECS Transactions, 2010, 33, 379-387.	0.3	2
97	Capture/Emission Processes of Carriers in Heterointerface Traps Observed in the Transient Charge-Pumping Characteristics of SiGe/Si-Hetero-Channel pMOSFETs. Key Engineering Materials, 0, 470, 201-206.	0.4	2
98	(Invited) Atomically Controlled CVD Processing for Doping in Future Si-Based Devices. ECS Transactions, 2011, 37, 181-188.	0.3	2
99	Behavior of N atoms after thermal nitridation of Si1â^'xGex surface. Thin Solid Films, 2012, 520, 3392-3396.	0.8	2
100	(Invited) Atomically Controlled CVD Processing of Group IV Semiconductors for Strain Engineering and Doping in Ultralarge Scale Integration. ECS Transactions, 2013, 54, 55-64.	0.3	2
101	Electrical properties and B depth profiles of in-situ B doped Si films grown by ECR Ar plasma CVD without substrate heating. Materials Science in Semiconductor Processing, 2017, 70, 50-54.	1.9	2
102	Quantum Associative Memory with Quantum Neural Network via Adiabatic Hamiltonian Evolution. IEICE Transactions on Information and Systems, 2017, E100.D, 2683-2689.	0.4	2
103	Learning Rule for a Quantum Neural Network Inspired by Hebbian Learning. IEICE Transactions on Information and Systems, 2021, E104.D, 237-245.	0.4	2
104	Strain Control of Stripe Patterned Si/Si1-xGex/Si(100) Heterostructures. ECS Transactions, 2006, 3, 421-427.	0.3	1
105	Atomically Controlled Processing for Group IV Semiconductors. ECS Transactions, 2009, 22, 111-120.	0.3	1
106	Atomically controlled CVD processing of group IV semiconductors for ultra-large-scale integrations. Advances in Natural Sciences: Nanoscience and Nanotechnology, 2012, 3, 023002.	0.7	1
107	Majority neuron circuit having large fan-in with non-volatile synaptic weight. , 2014, , .		1
108	Nitrogen doping effect upon hole tunneling characteristics of Si barriers in Si1-xGex/Si resonant tunneling diode. Thin Solid Films, 2014, 557, 302-306.	0.8	1

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109	Neuro-inspired quantum associative memory using adiabatic hamiltonian evolution. , 2017, , .		1
110	Electron-cyclotron resonance Ar plasma-induced electrical activation of B atoms without substrate heating in B doped Si epitaxial films on Si(100). Materials Science in Semiconductor Processing, 2020, 107, 104823.	1.9	1
111	Silicon atomic layer growth using flash heating in CVD. European Physical Journal Special Topics, 1993, 03, C3-449-C3-456.	0.2	1
112	X-Ray Photoemission Study of SiO₂/Si/Si_{0.55}Ge_{0.45}/Si Heterostructures. IEICE Transactions on Electronics, 2013, E96.C, 680-685.	0.3	1
113	Si Epitaxial Growth on the Atomic-Order Nitrided Si(100) Surface in SiH4 Reaction. , 2003, , 139-144.		1
114	Separation by bonding Si Islands (SBSI) for LSI applications. Materials Science in Semiconductor Processing, 2005, 8, 59-63.	1.9	0
115	High Performance pMOSFETs with High Ge Fraction Strained SiGe-heterostructure-channel and Ultrashallow Source/Drain Formed by Selective B-Doped SiGe CVD. IEEJ Transactions on Electronics, Information and Systems, 2006, 126, 1079-1082.	0.1	0
116	Surface reaction and B atom segregation in ECR chlorine plasma etching of B-doped Si1â^'xGex epitaxial films. Thin Solid Films, 2006, 508, 301-304.	0.8	0
117	Atomic-Order Thermal Nitridation of Si1-xGex(100) at Low Temperatures by NH3. ECS Transactions, 2006, 3, 1205-1210.	0.3	0
118	Atomically controlled CVD technology for group IV semiconductors. , 2006, , .		0
119	Strain Control of Si and Si1-xGex Layers in the Si/Si1-xGex/Si Heterostructures by Stripe-Shape Patterning for Future Si-Based Devices. ECS Transactions, 2007, 11, 91-99.	0.3	0
120	Highâ€performance pMOSFETs with high Ge fraction strained SiGeâ€heterostructure channel and ultrashallow source/drain formed by selective Bâ€doped SiGe CVD. Electrical Engineering in Japan (English Translation of Denki Gakkai Ronbunshi), 2008, 165, 46-50.	0.2	0
121	Atomically controlled CVD processing for future Si-based devices. , 2008, , .		0
122	Atomically Controlled CVD Processing for Doping of Si-Based Group IV Semiconductors. ECS Transactions, 2009, 25, 177-184.	0.3	0
123	Atomically Controlled Plasma Processing for Epitaxial Growth of Group IV Semiconductor Nanostructures. ECS Transactions, 2009, 25, 229-236.	0.3	0
124	Atomically controlled plasma processing for epitaxial growth of group IV semiconductors. , 2010, , .		0
125	Atomically controlled processing in strained Si-based CVD epitaxial growth. , 2010, , .		0
126	Atomically Controlled Plasma Processing for Quantum Heterointegration of Group IV Semiconductors. ECS Transactions, 2011, 41, 337-343.	0.3	0

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127	Atomically Controlled Formation of Strained Si1-xGex/Si Quantum Heterostructure for Room-Temperature Resonant Tunneling Diode. ECS Transactions, 2011, 41, 309-314.	0.3	0
128	Atomically controlled CVD technology of group IV semiconductors for ultralarge scale integration. , 2012, , .		0
129	Strain Control of Si and Si1-yCy Layers in Si/Si1-yCy/Si(100) Heterostructures. , 2012, , .		0
130	(Invited) Group-IV Semiconductor Quantum Heterointegration by Low-Energy Plasma CVD Processing. ECS Transactions, 2013, 58, 195-200.	0.3	0
131	Formation and Characterization of Strained Si1-XGex Films Epitaxially Grown on Si(100) by Low-Energy ECR Ar Plasma CVD without Substrate Heating. ECS Transactions, 2013, 58, 207-211.	0.3	0
132	Atomically controlled processing for nitrogen doping of group IV semiconductors. , 2014, , .		0
133	Hydrogen Atom Desorption Induced by Electron Bombardment on Si Surface. ECS Transactions, 2015, 69, 35-38.	0.3	0
134	C and Si delta doping in Ge by CH3SiH3 using reduced pressure chemical vapor deposition. Thin Solid Films, 2016, 602, 24-28.	0.8	0
135	Silicon-Carbon alloy film formation on Si(100) using SiH 4 and CH 4 reaction under low-energy ECR Ar plasma irradiation. Materials Science in Semiconductor Processing, 2017, 70, 188-192.	1.9	0
136	Heavy Doping Characteristics of Si Films Epitaxially Grown at 450Â°C by Alternately Supplied PH3 and SiH4. , 2003, , 145-150.		0
137	SiGeç³»ã‚¨ãƒ”ã‚¿ã‚ã‚·ãƒ£ãƒ«æˆé•·ã•ãšåŽŸå±±å^¶å¾¡. Shinku/Journal of the Vacuum Society of Japan, 2005, 48, 8-12.	0.2	0
138	Separation by Bonding Si Islands (SBSI) for Advanced CMOS LSI Applications. IEICE Transactions on Electronics, 2005, E88-C, 656-661.	0.3	0
139	CMOS Majority Circuit with Large Fan-In. IEICE Transactions on Electronics, 2016, E99.C, 1056-1064.	0.3	0
140	Complexity Reduction of Neural Network Model for Local Motion Detection in Motion Stereo Vision. Lecture Notes in Computer Science, 2017, , 830-839.	1.0	0
141	(Invited) Low-Energy Plasma Enhanced Chemical Vapor Deposition and In-Situ Doping for Junction Formation in Group-IV Semiconductor Devices. ECS Meeting Abstracts, 2019, , .	0.0	0